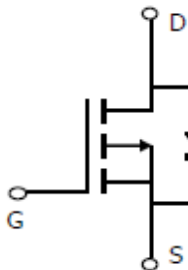
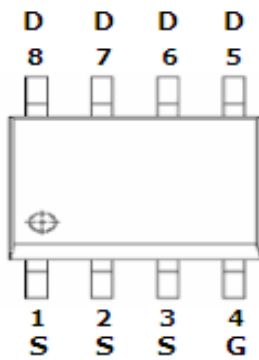


**DESCRIPTION**

The STP4407 is the P-Channel logic enhancement mode power field effect transistor is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other batter powered circuits where high-side switching.

**PIN CONFIGURATION  
SOP-8**

**FEATURE**

- -30V/-10A,  $R_{DS(ON)} = 15m\Omega$   
@ $V_{GS} = -10V$
- -30V/-6.0A,  $R_{DS(ON)} = 24m\Omega$   
@ $V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP-8 package design

**PART MARKING**


**Y : Year Code**  
**A : Produce Code**  
**B : Process Code**



**STP4407** 

P Channel Enhancement Mode MOSFET  
- 10A

**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C Unless otherwise noted )

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	VDSS	-30	V
Gate-Source Voltage	VGSS	±20	V
Continuous Drain Current (TJ=150°C)	ID	TA=25°C -10	A
		TA=70°C -6	
Pulsed Drain Current	IDM	-50	A
Continuous Source Current (Diode Conduction)	IS	-20	A
Power Dissipation	PD	TA=25°C 2.5	W
		TA=70°C 2.0	
Operation Junction Temperature	TJ	-55/150	°C
Storage Temperature Range	TSTG	-55/150	°C
Thermal Resistance-Junction to Ambient	RθJA	50	°C/W

**ELECTRICAL CHARACTERISTICS** ( Ta = 25°C Unless otherwise noted )

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-2.5	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$ $T_J=55^\circ C$	$V_{DS}=-30V, V_{GS}=0V$			-1	uA
		$V_{DS}=-30V, V_{GS}=0V$			-5	
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-10A$		15	20	mΩ
		$V_{GS}=-4.5V, I_D=-6.0A$		24	32	
Forward Transconductance	$g_{fs}$	$V_{DS}=-5V, I_D=-10A$		26		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.0A, V_{GS}=0V$			-1	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		30		nC
Gate-Source Charge	$Q_{gs}$			4.3		
Gate-Drain Charge	$Q_{gd}$			10		
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		2076	2500	pF
Output Capacitance	$C_{oss}$			400		
Reverse Transfer Capacitance	$C_{rss}$			302		
Turn-On Time	$t_{d(on)}$ $t_r$	$V_{DD}=15V, R_L=1.25\Omega$ $I_D=-1A, V_{GEN}=-10V$ $R_G=3\Omega$		10.4		nS
				24		
Turn-Off Time	$t_{d(off)}$ $t_f$			12.6		
				12		

**TYPICAL CHARACTERISTICS**

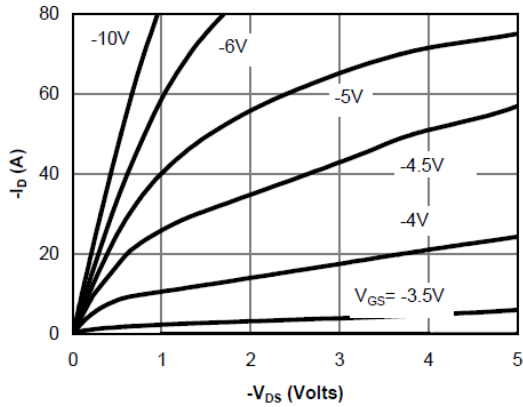


Figure 1: On-Region Characteristics

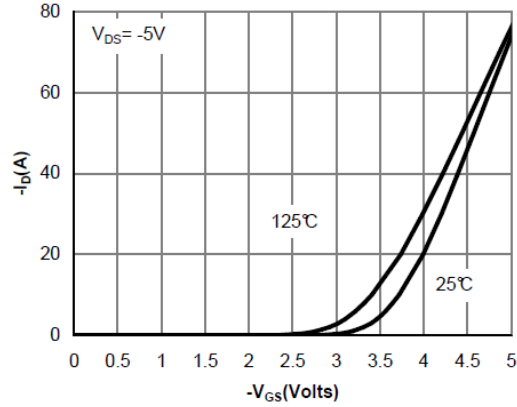


Figure 2: Transfer Characteristics

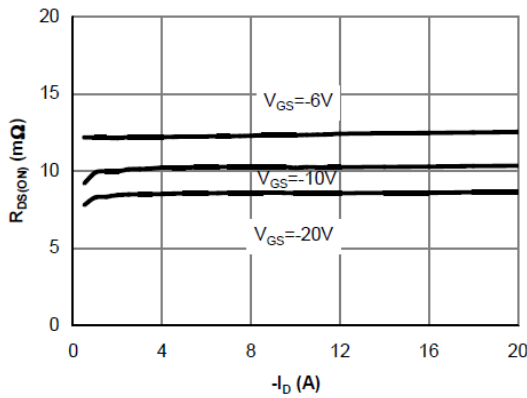


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

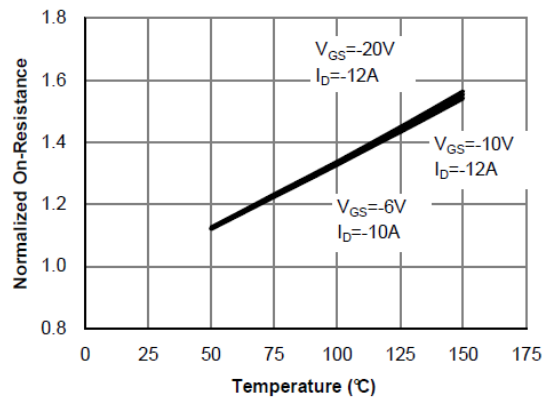


Figure 4: On-Resistance vs. Junction Temperature

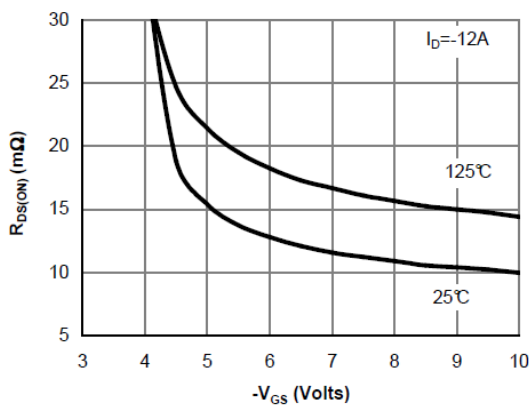


Figure 5: On-Resistance vs. Gate-Source Voltage

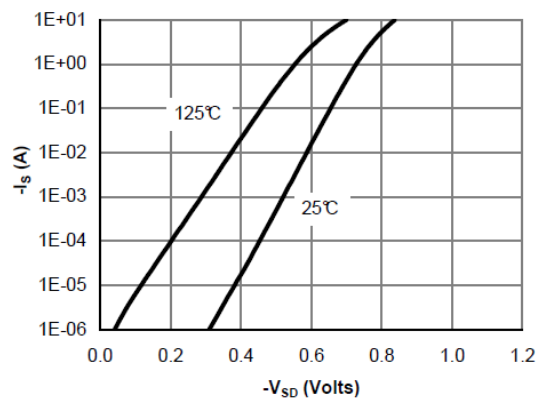


Figure 6: Body-Diode Characteristics

**TYPICAL CHARACTERISTICS**

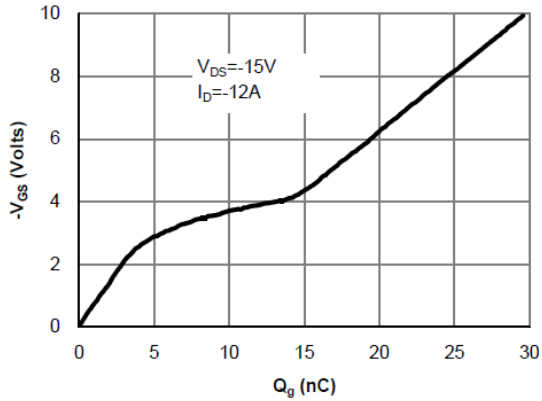


Figure 7: Gate-Charge Characteristics

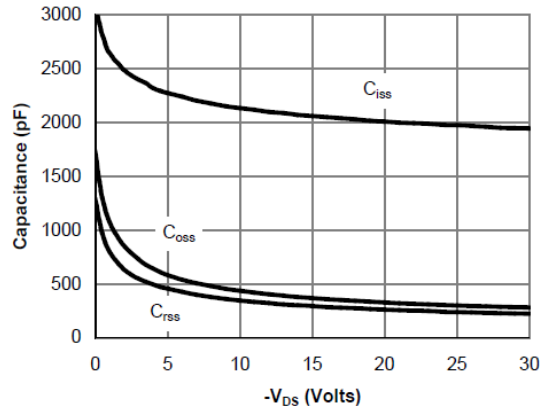


Figure 8: Capacitance Characteristics

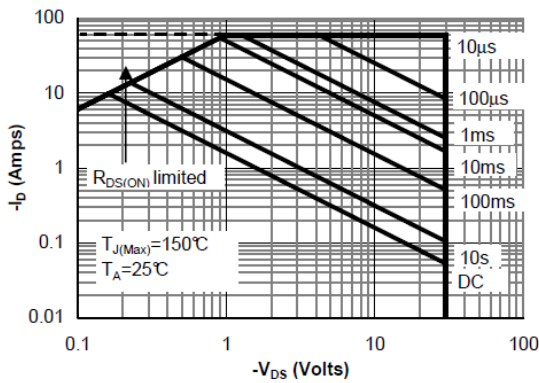


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

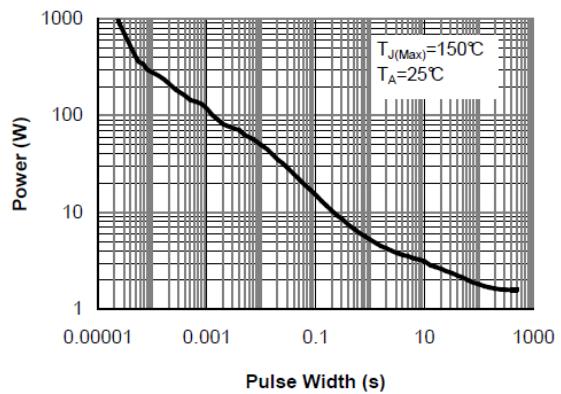


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

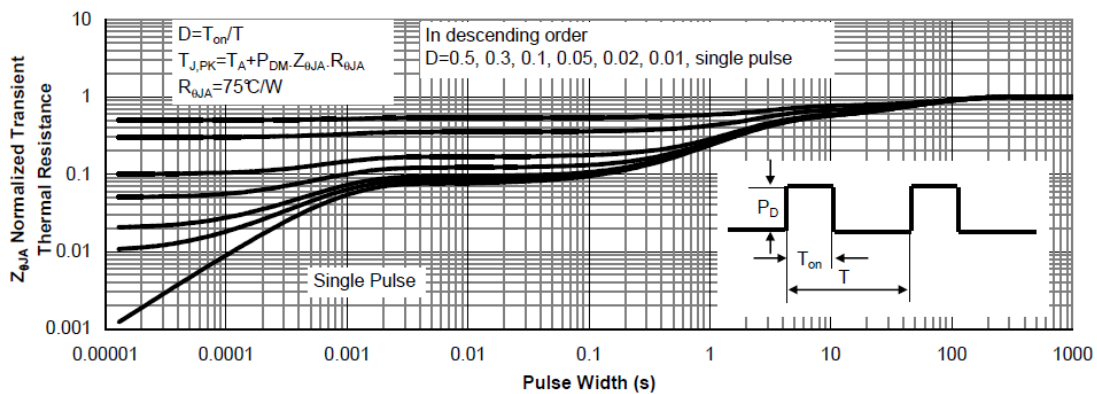
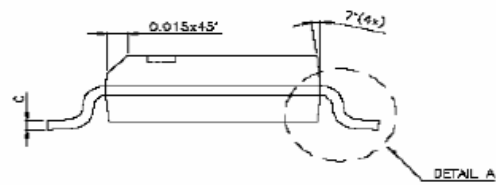
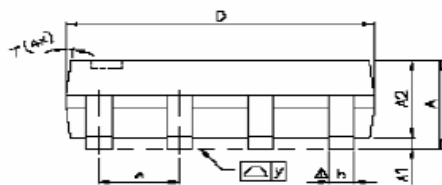
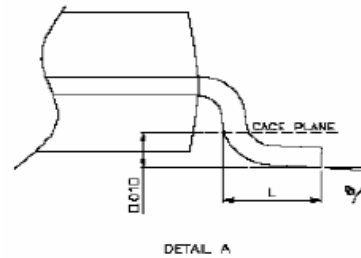
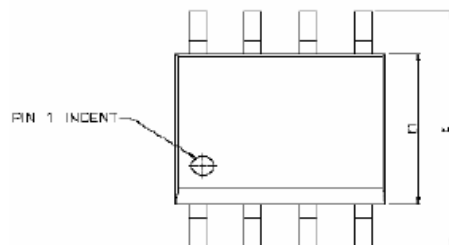


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

**PACKAGE OUTLINE SOP-8P**


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
$\Delta$ y	—	—	0.076	—	—	0.003
$\theta$	0°	—	8°	0°	—	8°